# **Voltage Regulator** - Low Noise, LDO Linear

# 150 mA

The NCP4688 is a CMOS 150 mA LDO linear voltage regulator with high output voltage accuracy which features a low noise output voltage and high ripple rejection. The low level of output noise 10  $\mu Vrms$  typically is kept at any output voltage. The very common SOT23–5 package and small  $\mu DFN$  1x1 package are suitable for industrial applications, portable communication equipments and RF modules.

#### **Features**

• Operating Input Voltage Range: 2 V to 5.25 V

• Output Voltage Range: 1.2 to 4.8 V (available in 0.1 V steps)

• ±1% Output Voltage Accuracy

Output Noise: 10 μVrmsLine Regulation: 0.02%/V

• Current Limit Circuit

• High PSRR: 80 dB at 1 kHz, 75 dB at 10 kHz

• Available in SOT-23-5 and µDFN 1.0 x 1.0 mm Package

• These are Pb-Free Devices

# **Typical Applications**

• Home Appliances, Industrial Equipment

• Cable Boxes, Satellite Receivers, Entertainment Systems

• Car Audio Equipment, Navigation Systems

 Notebook Adaptors, LCD TVs, Cordless Phones and Private LAN Systems

• RF Modules

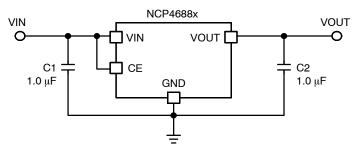


Figure 1. Typical Application Schematic



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# MARKING DIAGRAMS



SOT-23-5 CASE 1212





CASE 517BR



(Top Views)

XX, XXX = Specific Device Code M, MM = Date Code

■ = Date Code ■ = Pb–Free Package

(\*Note: Microdot may be in either location)

#### ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 12 of this data sheet.

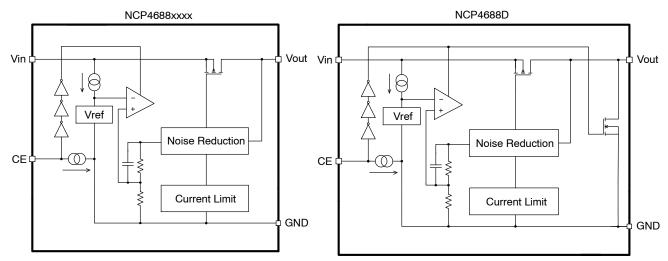


Figure 2. Simplified Schematic Block Diagram

**Table 1. PIN FUNCTION DESCRIPTION** 

Pin No. SOT-23-5	Pin No. DFN 1x1	Pin Name	Description
1	4	VIN	Input pin
2	2	GND	Ground pin
3	3	CE	Chip enable pin ("H" active)
4		NC	Non connected
5	1	VOUT	Output pin
	*EP	EP	Exposed Pad (leave floating or connect to GND)

**Table 2. ABSOLUTE MAXIMUM RATINGS** 

Rating	Symbol	Value	Unit
Input Voltage	V <sub>IN</sub>	0 – 6 V	V
Output Voltage	V <sub>OUT</sub>	-0.3 to V <sub>IN</sub> + 0.3	V
Chip Enable Input	V <sub>CE</sub>	0 – 6 V	V
Power Dissipation SOT-23-5	P <sub>D</sub>	420	mW
Power Dissipation μDFN 1.0 x 1.0 mm	7	400	
Junction Temperature	TJ	-40 to 150	°C
Storage Temperature	T <sub>STG</sub>	-55 to 125	°C
ESD Capability, Human Body Model (Note 1)	ESD <sub>HBM</sub>	2000	V
ESD Capability, Machine Model (Note 1)	ESD <sub>MM</sub>	200	V

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

- This device series incorporates ESD protection and is tested by the following methods:
  - ESD Human Body Model tested per AEC-Q100-002 (EIA/JÉSD22-A114)
  - ESD Machine Model tested per AEC-Q100-003 (EIA/JESD22-A115)
  - Latchup Current Maximum Rating tested per JEDEC standard: JESD78

# **Table 3. THERMAL CHARACTERISTICS**

Rating	Symbol	Value	Unit
Thermal Characteristics, SOT-23-5 Thermal Resistance, Junction-to-Air	$R_{ heta JA}$	238	°C/W
Thermal Characteristics, μDFN 1x1 Thermal Resistance, Junction-to-Air	$R_{ heta JA}$	250	°C/W

**Table 4. ELECTRICAL CHARACTERISTICS** ( $-40^{\circ}C \le T_{A} \le 85^{\circ}C$ ;  $C_{IN} = C_{OUT} = 1.0~\mu\text{F}$ , unless otherwise noted. Typical values are at  $T_{A} = +25^{\circ}C$ .)

Parameter	Test Conditions		Symbol	Min	Тур	Max	Unit
Operating Input Voltage	1.2 V < Vout < 4.8 V		V <sub>IN</sub>	2.0		5.25	V
Output Voltage	Ta = 25°C, Vout > 2.0 V	V <sub>OUT</sub>	x0.99		x1.01	V	
	-40°C < Ta < 85°C, Vout > 2.0		x0.985		x1.015	V	
	Ta = 25°C, Vout ≤ 2.0 V		-20		+20	mV	
	-40°C < Ta < 85°C, Vout ≤ 2.0	) V		-30		+30	mV
Output Voltage Temp. Coefficient	-40°C < Ta < 85°C				±100		ppm/°C
Line Regulation	Set Vout + 0.3 < VIN < 5.25 V	Vout > 4.1 V	Line <sub>Reg</sub>		0.02	0.10	%/V
	Set Vout + 0.5 < VIN < 5.0 V	1.7 V ≤ V <sub>OUT</sub> < 4.1 V					
	2.2 < VIN < 5.0 V	Vout < 1.7 V					
Load Regulation	1 mA < I <sub>OUT</sub> ≤ 150 mA		Load <sub>Reg</sub>	-14	0	14	mV
Dropout Voltage	I <sub>OUT</sub> = 150 mA	1.2 V ≤ V <sub>OUT</sub> < 1.3 V	V <sub>DO</sub>		0.39	0.80	V
		1.3 V ≤ V <sub>OUT</sub> < 1.4 V	=		0.37	.37 0.70	
		1.4 V ≤ V <sub>OUT</sub> ≤ 1.5 V			0.34	0.60	
		1.5 V ≤ V <sub>OUT</sub> < 1.7 V			0.32	0.50	
		1.7 V ≤ V <sub>OUT</sub> < 2.0 V			0.29	0.41	
		2.0 V ≤ V <sub>OUT</sub> < 2.5 V			0.25	0.36	
		2.5 V ≤ V <sub>OUT</sub> < 2.8 V			0.22	0.31	
		2.8 V ≤ V <sub>OUT</sub> ≤ 4.8 V			0.20	0.28	
Output Current			I <sub>OUT</sub>	150			mA
Short Current Limit	V <sub>OUT</sub> = 0 V		I <sub>SC</sub>		40		mA
Quiescent Current	lout = 0 mA	Vout > 4.1 V	IQ		80	100	μΑ
		Vout ≤ 4.1 V			75		
Standby Current	$V_{IN} = V_{IN \text{ max}}$ , $V_{CE} = 0 \text{ V}$		I <sub>STB</sub>		0.1	1.0	μΑ
CE Pin Pull-Down Current			I <sub>PD</sub>		0.3	0.6	μΑ
CE Pin Threshold Voltage	CE Input Voltage "H"		V <sub>CEH</sub>	1.0		V <sub>IN</sub>	V
	CE Input Voltage "L"		V <sub>CEL</sub>			0.4	
Power Supply	V <sub>OUT</sub> > 4.1 V @ V <sub>IN</sub> = 5.25 V,	f = 1 kHz	PSRR		80		dB
Rejection Ratio	$V_{OUT} \le 4.1 \text{ V } @ V_{IN} = $ Set $V_{OUT} + 1.0 \text{ V},$	f = 10 kHz			75		
	$\Delta V_{IN\_PK-PK} = 0.2 \text{ V},$ $I_{OUT} = 30 \text{ mA}$	f = 100 kHz			65		
Output Noise Voltage	I <sub>OUT</sub> = 30 mA, f = 10 Hz to 10	0 kHz	V <sub>NOISE</sub>		10		$\mu V_{rms}$
Autodischarge NMOS Resistance	V <sub>IN</sub> = 4.0 V, V <sub>CE</sub> = 0.0 V		R <sub>DSON</sub>		60		ohm

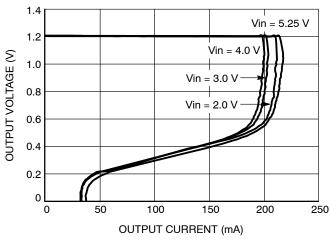


Figure 3. Output Voltage vs. Output Current NCP4688xx12

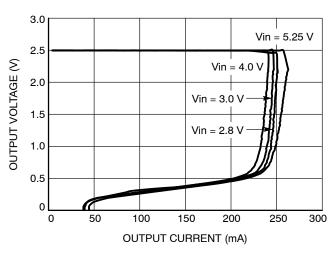


Figure 4. Output Voltage vs. Output Current NCP4688xx25

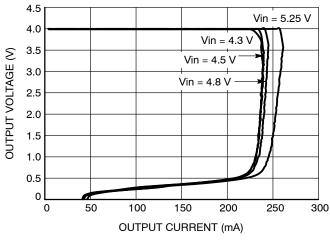


Figure 5. Output Voltage vs. Output Current NCP4688xx40

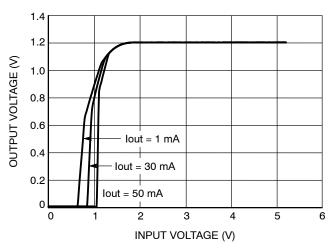


Figure 6. Output Voltage vs. Input Voltage NCP4688xx12

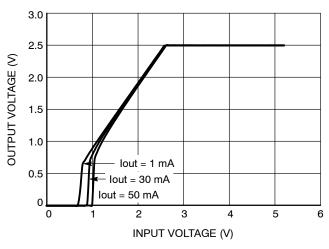


Figure 7. Output Voltage vs. Input Voltage NCP4688xx25

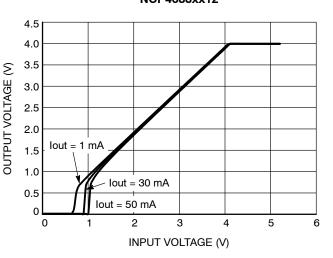


Figure 8. Output Voltage vs. Input Voltage NCP4688xx40

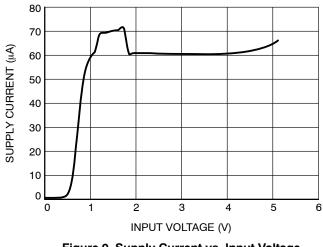


Figure 9. Supply Current vs. Input Voltage NCP4688xx12

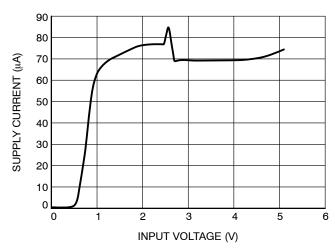


Figure 10. Supply Current vs. Input Voltage NCP4688xx25

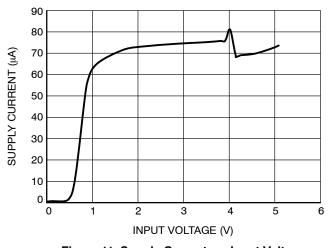


Figure 11. Supply Current vs. Input Voltage NCP4688xx40

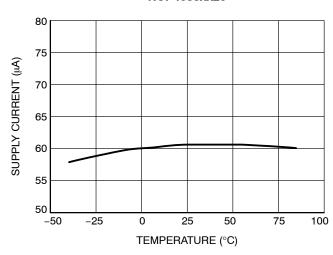


Figure 12. Supply Current vs. Temperature NCP4688xx12

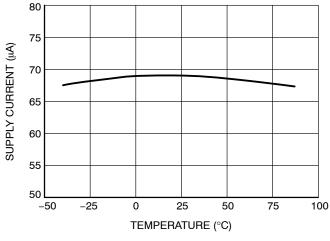


Figure 13. Supply Current vs. Temperature NCP4688xx25

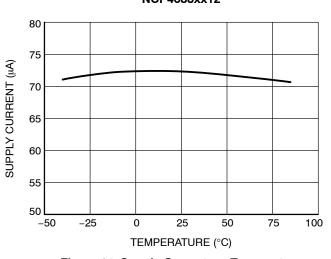
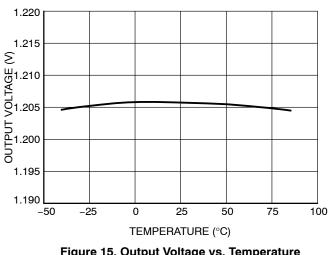


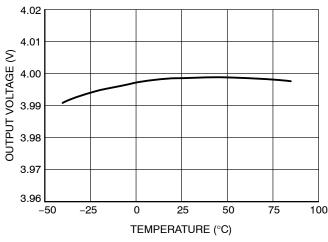
Figure 14. Supply Current vs. Temperature NCP4688xx40



2.53 2.52 By 2.51 2.50 2.49 2.48 2.47 -50 -25 0 25 50 75 100 TEMPERATURE (°C)

Figure 15. Output Voltage vs. Temperature NCP4688xx12

Figure 16. Output Voltage vs. Temperature NCP4688xx25



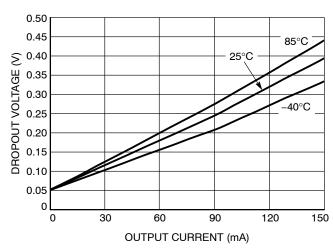
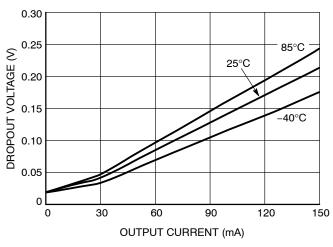


Figure 17. Output Voltage vs. Temperature NCP4688xx40

Figure 18. Dropout Voltage vs. Output Current NCP4688xx12



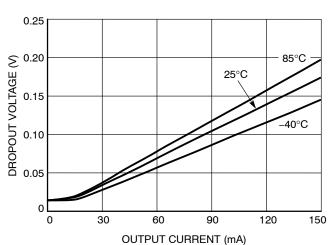
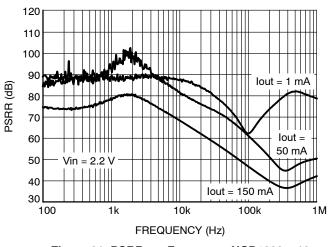


Figure 19. Dropout Voltage vs. Output Current NCP4688xx25

Figure 20. Dropout Voltage vs. Output Current NCP4688xx40

# **TYPICAL CHARACTERISTICS**

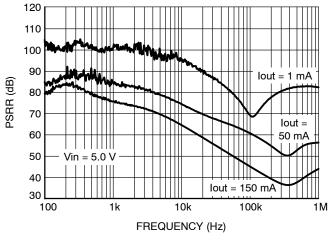
120



110 100 lout = 1 mA90 PSRR (dB) 80 70 lout = 60 50 mA 50 Vin = 3.5 V40 lout = 150 mA 30 100k 100 1k 10k 1M FREQUENCY (Hz)

Figure 21. PSRR vs. Frequency NCP4688xx12

Figure 22. PSRR vs. Frequency NCP4688xx25



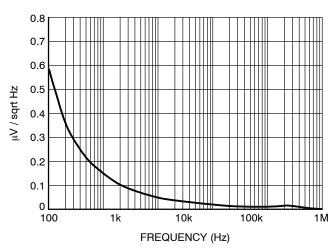
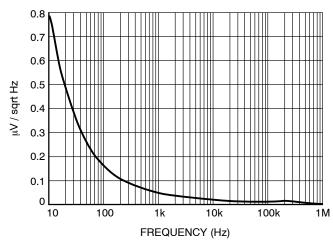


Figure 23. PSRR vs. Frequency NCP4688xx40

Figure 24. Output Noise Density vs. Frequency NCP4688xx12



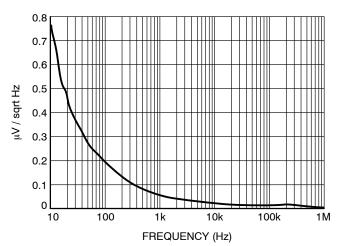


Figure 25. Output Noise Density vs. Frequency NCP4688xx25

Figure 26. Output Noise Density vs. Frequency NCP4688xx40

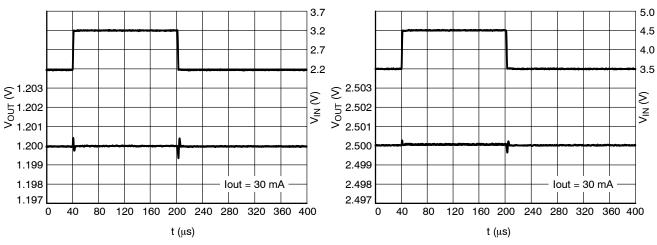


Figure 27. Line Transient Response NCP4688xx12

Figure 28. Line Transient Response NCP4688xx25

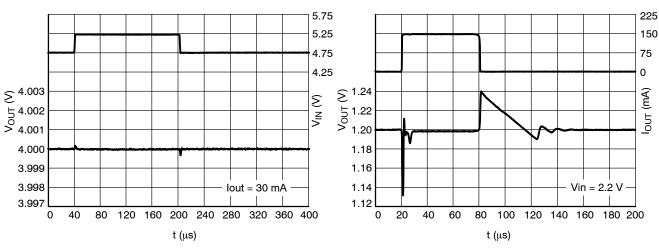


Figure 29. Line Transient Response NCP4688xx40

Figure 30. Load Transient Response Load Step 1 mA to 150 mA NCP4688xx12

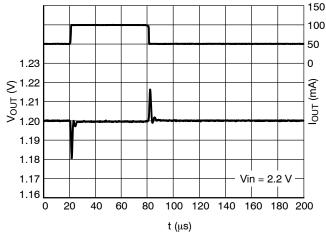


Figure 31. Load Transient Response Load Step 50 mA to 100 mA NCP4688xx12

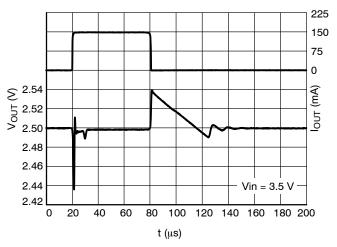
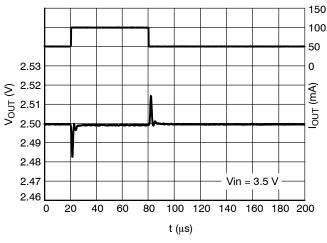


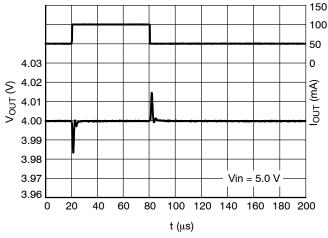
Figure 32. Load Transient Response Load Step 1 mA to 150 mA NCP4688xx25



225 150 75 4.06 0 5 4.02 > 4.00 50 3.98 3.96 3.94 Vin = 5.0 V3.92 40 20 60 80 100 120 140 160 180 200 t (μs)

Figure 33. Load Transient Response Load Step 50 mA to 100 mA NCP4688xx25

Figure 34. Load Transient Response Load Step 1 mA to 150 mA NCP4688xx40



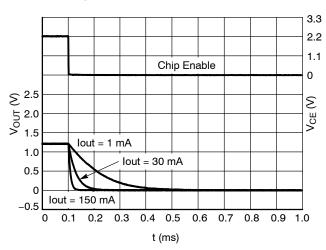
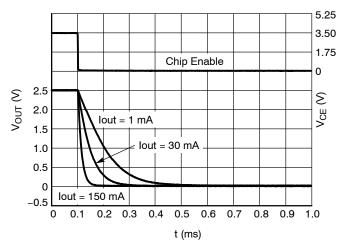


Figure 35. Load Transient Response Load Step 50 mA to 100 mA NCP4688xx40

Figure 36. Turn Off with CE Behavior NCP4688Dx12



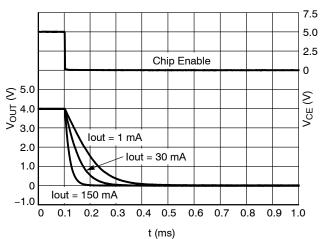


Figure 37. Turn Off with CE Behavior NCP4688Dx25

Figure 38. Turn Off with CE Behavior NCP4688Dx40

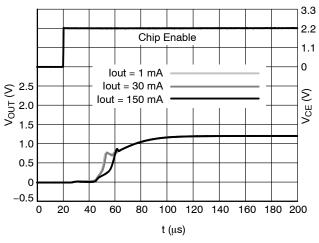


Figure 39. Turn ON with CE Behavior NCP4688xx12

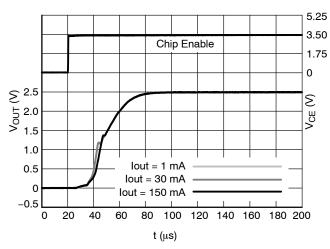


Figure 40. Turn ON with CE Behavior NCP4688xx25

# APPLICATION INFORMATION

A typical application circuit for NCP4688 series is shown in the Figure 41.

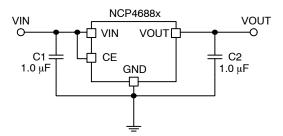


Figure 41. Typical Application Schematic

# Input Decoupling Capacitor (C1)

A  $1.0~\mu F$  ceramic input decoupling capacitor should be connected as close as possible to the input and ground pin of the NCP4688 device. Higher values and lower ESR improves line transient response.

# **Output Decoupling Capacitor (C2)**

A 1.0  $\mu F$  ceramic output decoupling capacitor is sufficient to achieve stable operation of the device. If tantalum capacitor is used, and its ESR is high, the loop oscillation may result. For information about ESR see Figures 42, 43 and 44. The capacitor should be connected as close as possible to the output and ground pin. Larger values and lower ESR improves dynamic parameters.

# **Enable Operation**

The enable pin CE may be used for turning the regulator on and off. The IC is switched on when a high level voltage is applied to the CE pin. The enable pin has an internal pull down current source which assure off state of LDO in case the CE pin will stay floating. If the enable function is not needed connect CE pin to  $V_{\rm IN}$ .

The D version of the NCP4688 device includes a transistor between  $V_{OUT}$  and GND that is used for faster discharging of the output capacitor. This function is activated when the IC goes into disable mode.

#### **Thermal Consideration**

As a power across the IC increase, it might become necessary to provide some thermal relief. The maximum power dissipation supported by the device is dependent upon board design and layout. Mounting pad configuration on the PCB, the board material, and also the ambient temperature affect the rate of temperature increase for the part. When the device has good thermal conductivity through the PCB the junction temperature will be relatively low in high power dissipation applications.

# **ESR vs. Output Current**

When using the NCP4688 devices, consider the following points:

The relation between Output Current Iout and ESR of the output capacitor are shown below in Figures 42, 43 and 44. The conditions when the device performs stable operation are marked as the hatched area in the charts.

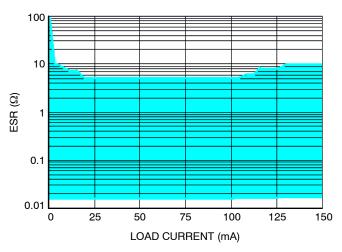


Figure 42. ESR vs. Load Current NCP4688xx12

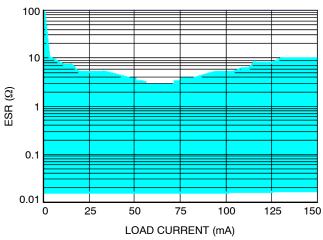


Figure 43. ESR vs. Load Current NCP4688xx25

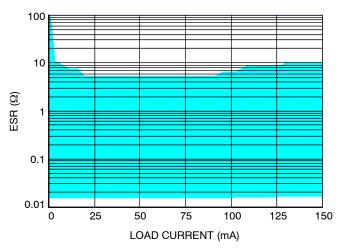


Figure 44. ESR vs. Load Current NCP4688xx40

# **ORDERING INFORMATION**

Device	Marking	Nominal Output Voltage	Feature	Package	Shipping <sup>†</sup>
NCP4688DMU12TCG	3A	1.2 V	Auto discharge	DFN1010 (Pb-Free)	10000 / Tape & Reel
NCP4688DMU15TCG	3E	1.5 V	Auto discharge	DFN1010 (Pb-Free)	10000 / Tape & Reel
NCP4688DMU18TCG	3H	1.8 V	Auto discharge	DFN1010 (Pb-Free)	10000 / Tape & Reel
NCP4688DMU25TCG	3R	2.5 V	Auto discharge	DFN1010 (Pb-Free)	10000 / Tape & Reel
NCP4688DMU28TCG	3U	2.8 V	Auto discharge	DFN1010 (Pb-Free)	10000 / Tape & Reel
NCP4688DMU30TCG	3X	3.0 V	Auto discharge	DFN1010 (Pb-Free)	10000 / Tape & Reel
NCP4688DMU33TCG	4A	3.3 V	Auto discharge	DFN1010 (Pb-Free)	10000 / Tape & Reel
NCP4688DSN12T1G	L12	1.2 V	Auto discharge	SOT-23 (Pb-Free)	3000 / Tape & Reel
NCP4688DSN15T1G	L15	1.5 V	Auto discharge	SOT-23 (Pb-Free)	3000 / Tape & Reel
NCP4688DSN18T1G	L18	1.8 V	Auto discharge	SOT-23 (Pb-Free)	3000 / Tape & Reel
NCP4688DSN25T1G	L25	2.5 V	Auto discharge	SOT-23 (Pb-Free)	3000 / Tape & Reel
NCP4688DSN28T1G	L28	2.8 V	Auto discharge	SOT-23 (Pb-Free)	3000 / Tape & Reel
NCP4688DSN33T1G	L33	3.3 V	Auto discharge	SOT-23 (Pb-Free)	3000 / Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

# **MECHANICAL CASE OUTLINE**

**PACKAGE DIMENSIONS** 



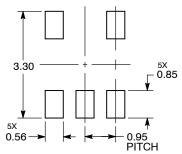


SOT-23 5-LEAD CASE 1212-01 **ISSUE A** 

**DATE 28 JAN 2011** 

# Α В 0.05 S 5X **b** L1 ⊕ 0.10 M C B S A S

#### RECOMMENDED **SOLDERING FOOTPRINT\***



DIMENSIONS: MILLIMETERS

- NOTES:
  1. DIMENSIONING AND TOLERANCING PER
  ASME Y14.5M, 1994.
  2. CONTROLLING DIMENSIONS: MILLIMETERS.
  3. DATUM C IS THE SEATING PLANE.

	MILLIMETERS		
DIM	MIN	MAX	
Α		1.45	
A1	0.00	0.10	
A2	1.00	1.30	
b	0.30	0.50	
C	0.10	0.25	
D	2.70	3.10	
E	2.50	3.10	
E1	1.50 1.80		
е	0.95 BSC		
L	0.20		
L1	0.45 0.75		

# **GENERIC MARKING DIAGRAM\***



XXX = Specific Device Code

= Date Code

= Pb-Free Package

(Note: Microdot may be in either location)

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

DOCUMENT NUMBER: 98ASH70518A		Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.		
DESCRIPTION:	SOT-23 5-LEAD		PAGE 1 OF 1	

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<sup>\*</sup>For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

# **MECHANICAL CASE OUTLINE**



# UDFN4 1.0x1.0, 0.65P CASE 517BR-01 **ISSUE O**

**DATE 27 OCT 2010** 

- NOTES:
  1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
  CONTROLLING DIMENSION: MILLIMETERS.
- DIMENSION 6 APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.15 AND
- 0.20 mm FROM TERMINAL.

4.	COPLANARITY APPLIES TO THE EXPOSED
	PAD AS WELL AS THE TERMINALS.

	MILLIMETERS			
DIM	MIN	MAX		
Α		0.60		
A1	0.00	0.05		
А3	0.10	REF		
b	0.20	0.30		
D	1.00	BSC		
D2	0.43	0.53		
E	1.00 BSC			
е	0.65	BSC		
L	0.20	0.30		
L2	0.27	0.37		
L3	0.02	0.12		

# **GENERIC MARKING DIAGRAM\***



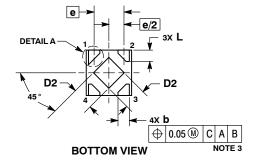
XX = Specific Device Code

MM = Date Code

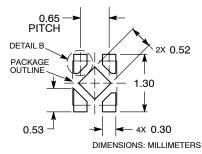
\*This information is generic. Please refer to device data sheet for actual part marking.

Pb-Free indicator, "G" or microdot " ■", may or may not be present.

#### 4X L3 В c 0.18 PIN ONE REFERENCE **DETAIL A** 0.05 2X 🗀 0.05 С 3X 0.43 4X 0.23 TOP VIEW (A3)0.05 C **≪** 3X 0 10 0.05 C **DETAIL B** C SEATING PLANE NOTE 4 SIDE VIEW



#### **RECOMMENDED MOUNTING FOOTPRINT\***



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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DESCRIPTION:	UDFN4, 1.0X1.0, 0.65P		PAGE 1 OF 1	

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